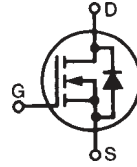


Linear L2™ Power MOSFET w/ Extended FBSOA

IXTK200N10L2 IXTX200N10L2

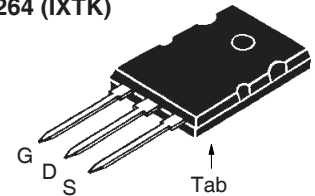
$V_{DSS} = 100V$
 $I_{D25} = 200A$
 $R_{DS(on)} \leq 11m\Omega$

N-Channel Enhancement Mode
 Guaranteed FBSOA
 Avalanche Rated

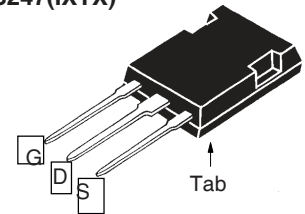


| Symbol | Test Conditions | Maximum Ratings | |
|------------|---|-------------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | 100 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$ | 100 | V |
| V_{GSS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ C$ (Chip Capability) | 200 | A |
| I_{LRMS} | Lead Current Limit, (RMS) | 160 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 500 | A |
| I_A | $T_C = 25^\circ C$ | 100 | A |
| E_{AS} | $T_C = 25^\circ C$ | 5 | J |
| P_D | $T_C = 25^\circ C$ | 1040 | W |
| T_J | | -55...+150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | -55...+150 | $^\circ C$ |
| T_L | 1.6mm (0.063 in.) from Case for 10s | 300 | $^\circ C$ |
| T_{SOLD} | Plastic Body for 10s | 260 | $^\circ C$ |
| M_d | Mounting Torque (IXTK) | 1.13/10 | Nm/lb.in. |
| F_C | Mounting Force (IXTX) | 20..120 / 4.5..27 | N/lb. |
| Weight | TO-264 | 10 | g |
| | PLUS247 | 6 | g |

TO-264 (IXTK)



PLUS247(IXTX)



G = Gate D = Drain
 S = Source Tab = Drain

Features

- Designed for Linear Operation
- Avalanche Rated
- Guaranteed FBSOA at $75^\circ C$

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Solid State Circuit Breakers
- Soft Start Controls
- Linear Amplifiers
- Programmable Loads
- Current Regulators

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|---------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 1mA$ | 100 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 3mA$ | 2.0 | | 4.5 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$ | | | 10 μA 250 μA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1 | | | 11 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | | |
|--------------|--|-----------------------|------|------|--------------------|
| | | Min. | Typ. | Max. | |
| g_{fs} | $V_{DS} = 10\text{V}$, $I_D = 60\text{A}$, Note 1 | 55 | 73 | 90 | S |
| C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 23 | | nF |
| C_{oss} | | | 3200 | | pF |
| C_{rss} | | | 610 | | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External) | | 40 | | ns |
| t_r | | | 225 | | ns |
| $t_{d(off)}$ | | | 127 | | ns |
| t_f | | | 27 | | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ | | 540 | | nC |
| Q_{gs} | | | 115 | | nC |
| Q_{gd} | | | 226 | | nC |
| R_{thJC} | | | | 0.12 | $^\circ\text{C/W}$ |
| R_{thCS} | | 0.15 | | | $^\circ\text{C/W}$ |

Safe-Operating-Area Specification

| Symbol | Test Conditions | Characteristic Values | | | |
|--------|--|-----------------------|------|------|---|
| | | Min. | Typ. | Max. | |
| SOA | $V_{DS} = 100\text{V}$, $I_D = 6.25\text{A}$, $T_C = 75^\circ\text{C}$, $t_p = 5\text{s}$ | 625 | | | W |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | | |
|----------|---|-----------------------|------|------|---------------|
| | | Min. | Typ. | Max. | |
| I_S | $V_{GS} = 0\text{V}$ | | | 200 | A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 800 | A |
| V_{SD} | $I_F = 100\text{A}$, $V_{GS} = 0\text{V}$, Note 1 | | | 1.4 | V |
| t_{rr} | $I_F = 100\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 50\text{V}$, $V_{GS} = 0\text{V}$ | | 245 | | ns |
| I_{RM} | | | 24.4 | | A |
| Q_{RM} | | | 3.0 | | μC |

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

ADVANCE TECHNICAL INFORMATION

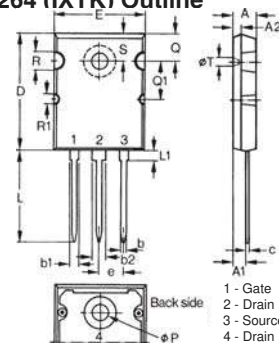
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

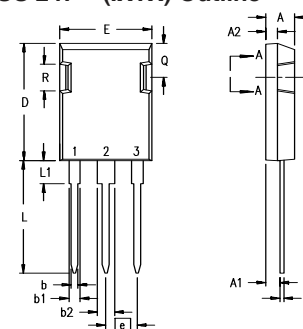
| | | | | | | | | | |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

TO-264 (IXTK) Outline



| Dim. | Millimeter | | Inches | |
|------|------------|-------|----------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.82 | 5.13 | .190 | .202 |
| A1 | 2.54 | 2.89 | .100 | .114 |
| A2 | 2.00 | 2.10 | .079 | .083 |
| b | 1.12 | 1.42 | .044 | .056 |
| b1 | 2.39 | 2.69 | .094 | .106 |
| b2 | 2.90 | 3.09 | .114 | .122 |
| c | 0.53 | 0.83 | .021 | .033 |
| D | 25.91 | 26.16 | 1.020 | 1.030 |
| E | 19.81 | 19.96 | .780 | .786 |
| e | 5.46 BSC | | .215 BSC | |
| J | 0.00 | 0.25 | .000 | .010 |
| K | 0.00 | 0.25 | .000 | .010 |
| L | 20.32 | 20.83 | .800 | .820 |
| L1 | 2.29 | 2.59 | .090 | .102 |
| P | 3.17 | 3.66 | .125 | .144 |
| Q | 6.07 | 6.27 | .239 | .247 |
| Q1 | 8.38 | 8.69 | .330 | .342 |
| R | 3.81 | 4.32 | .150 | .170 |
| R1 | 1.78 | 2.29 | .070 | .090 |
| S | 6.04 | 6.30 | .238 | .248 |
| T | 1.57 | 1.83 | .062 | .072 |

PLUS 247™ (IXTX) Outline



Terminals: 1 - Gate
2 - Drain
3 - Source

| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|----------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.83 | 5.21 | .190 | .205 |
| A ₁ | 2.29 | 2.54 | .090 | .100 |
| A ₂ | 1.91 | 2.16 | .075 | .085 |
| b | 1.14 | 1.40 | .045 | .055 |
| b ₁ | 1.91 | 2.13 | .075 | .084 |
| b ₂ | 2.92 | 3.12 | .115 | .123 |
| C | 0.61 | 0.80 | .024 | .031 |
| D | 20.80 | 21.34 | .819 | .840 |
| E | 15.75 | 16.13 | .620 | .635 |
| e | 5.45 BSC | | .215 BSC | |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | 3.81 | 4.32 | .150 | .170 |
| Q | 5.59 | 6.20 | .220 | 0.244 |
| R | 4.32 | 4.83 | .170 | .190 |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

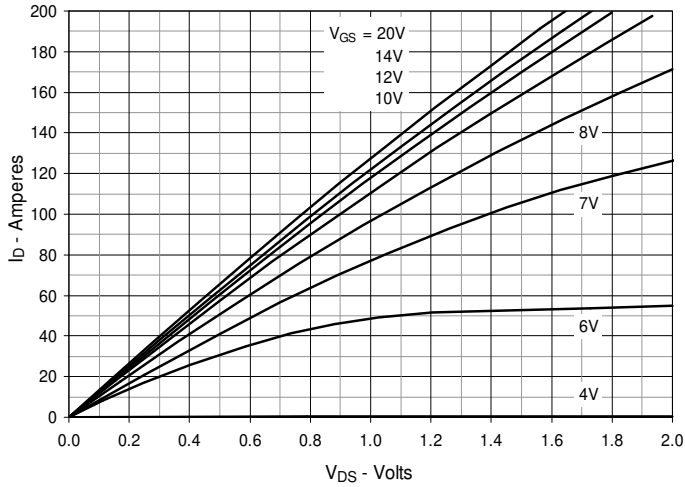


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

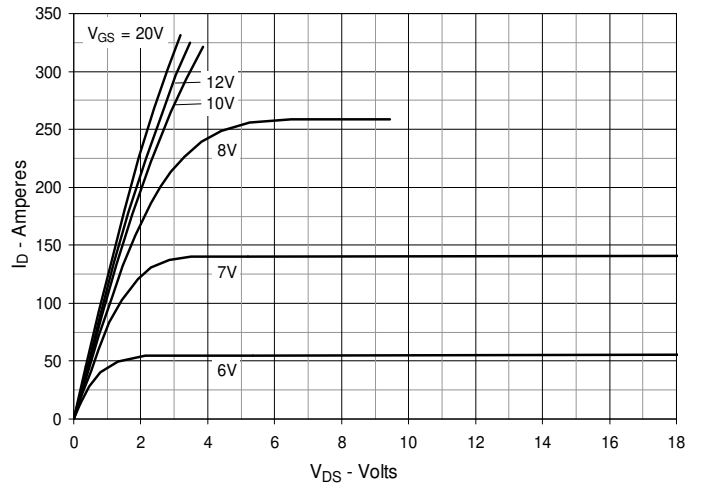


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

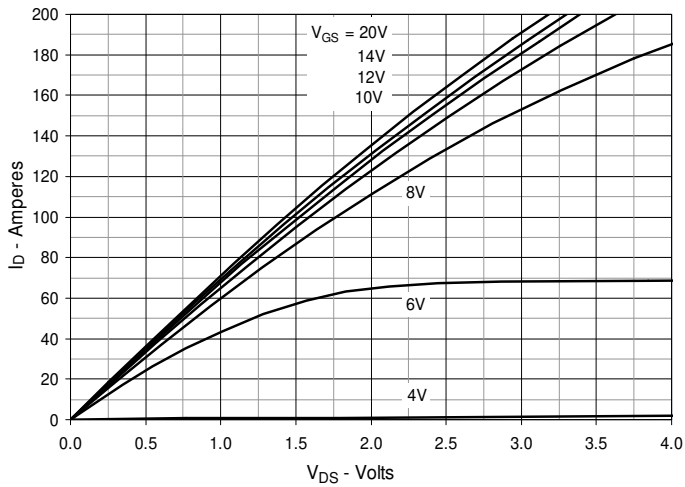


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 100\text{A}$ Value vs. Junction Temperature

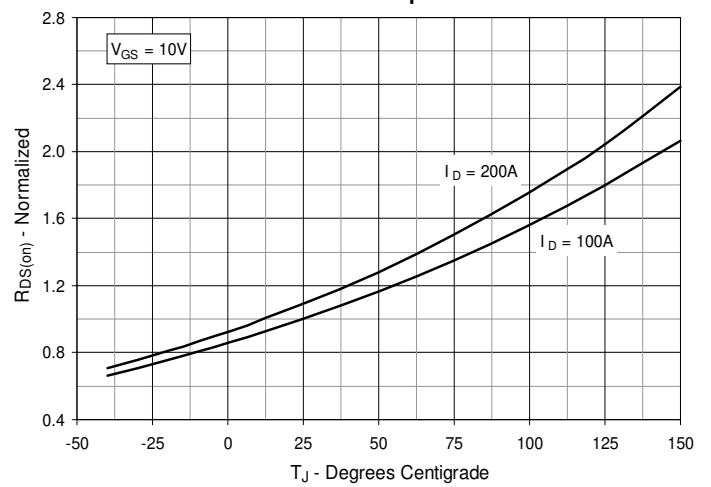


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 100\text{A}$ Value vs. Drain Current

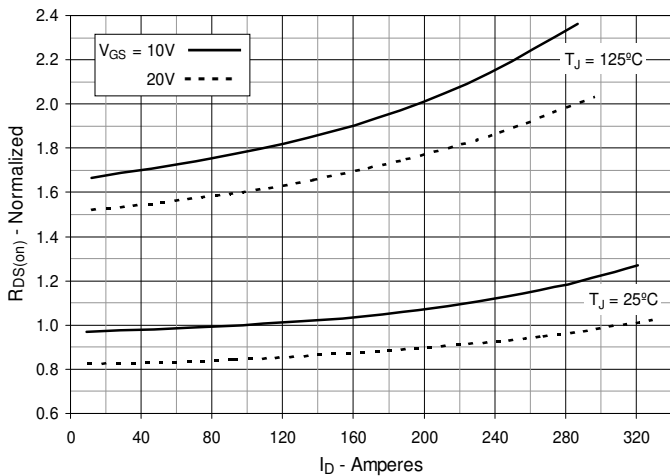


Fig. 6. Maximum Drain Current vs. Case Temperature

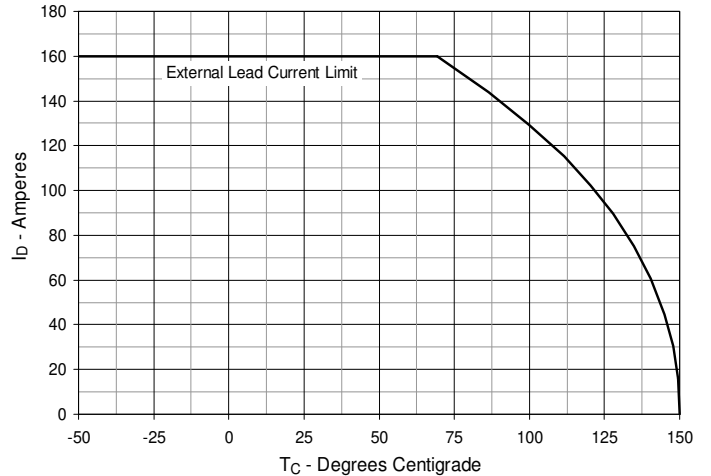


Fig. 7. Input Admittance

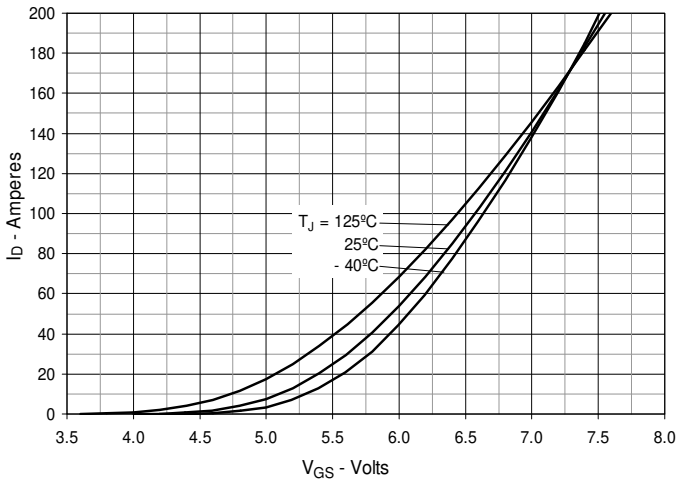


Fig. 8. Transconductance

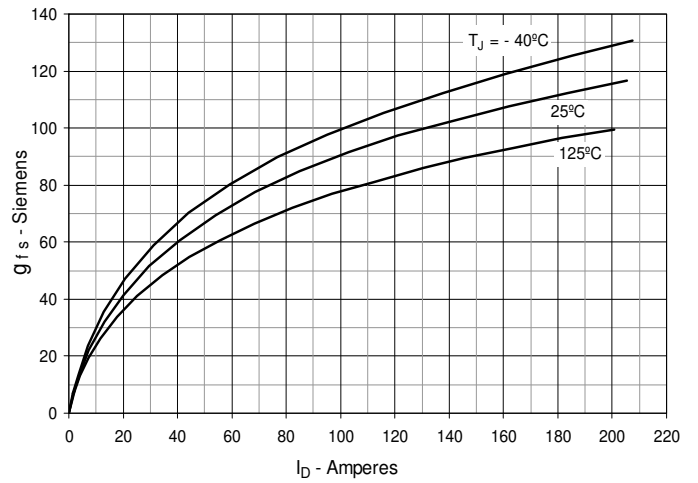


Fig. 9. Forward Voltage Drop of Intrinsic Diode

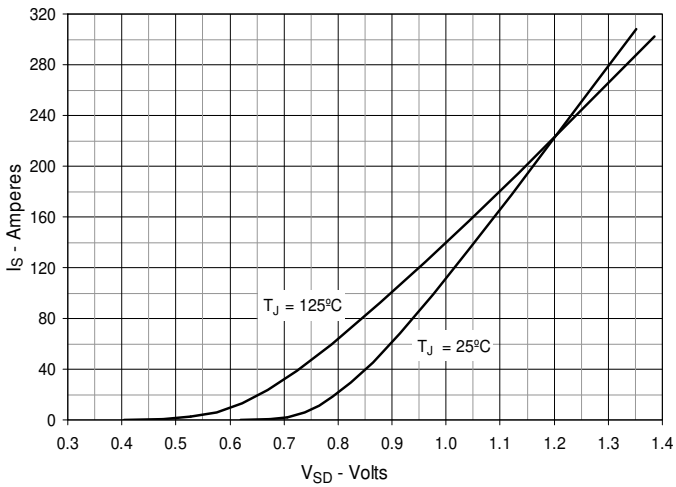


Fig. 10. Gate Charge

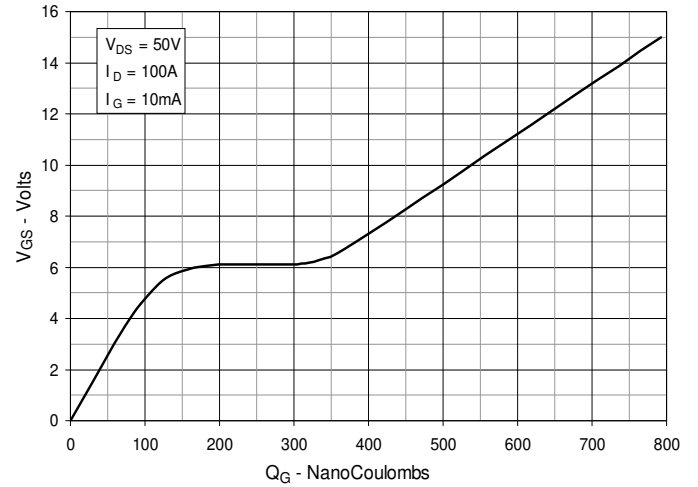


Fig. 11. Capacitance

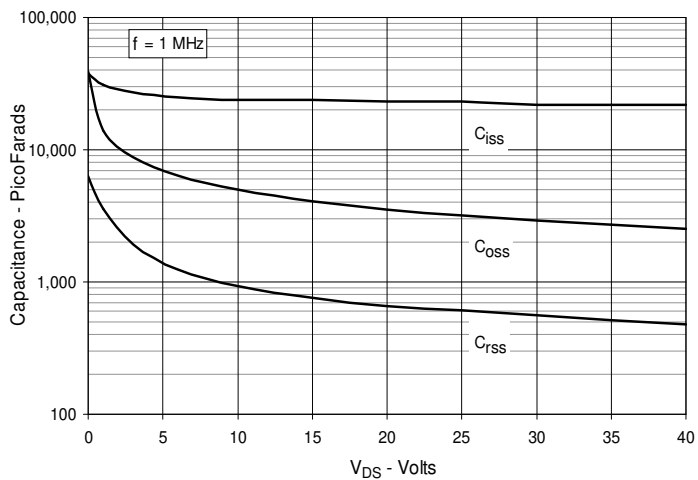


Fig. 12. Maximum Transient Thermal Impedance

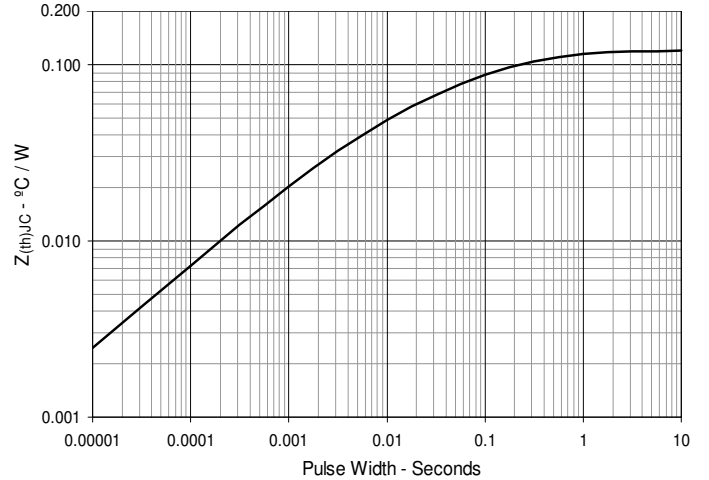


Fig. 13. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$

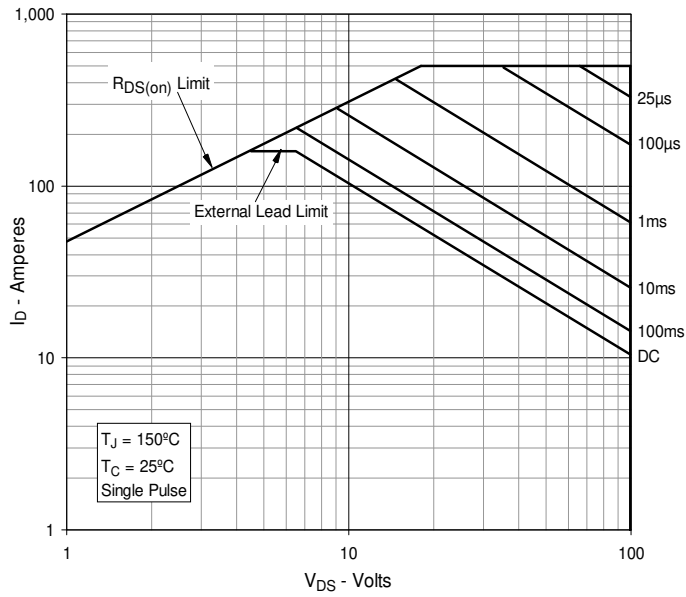
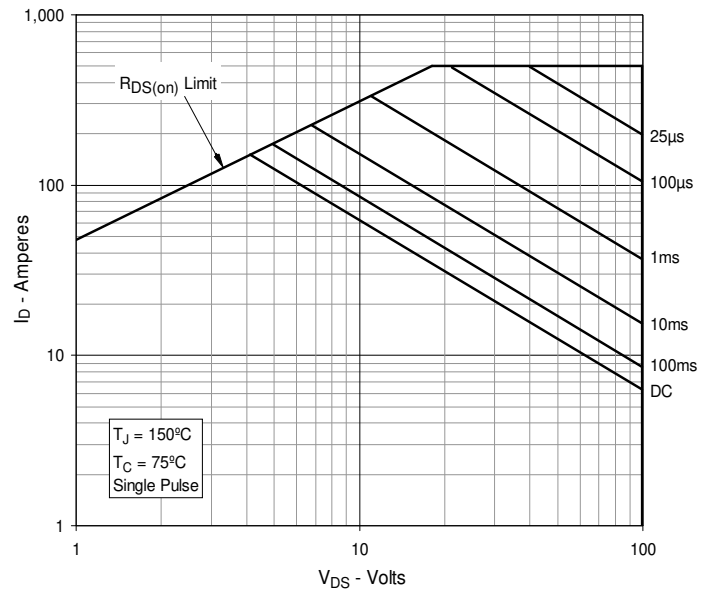


Fig. 14. Forward-Bias Safe Operating Area
@ $T_C = 75^\circ\text{C}$





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